

**A CAPACITOR FORMED ON A RECRYSTALLIZED
POLYSILICON LAYER AND A METHOD OF MANUFACTURE THEREFOR**

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device, a method of manufacture therefor, and an integrated circuit including the semiconductor device. The semiconductor device, among other elements, includes a recrystallized polysilicon layer 148 located over a gate electrode layer 143, a capacitor 170 located on the recrystallized polysilicon layer 148. The capacitor 170, in this embodiment, includes a first electrode 173, an insulator 175 located over the first electrode 173, and a second electrode 178 located over the insulator 175.